

Silicon NPN Power Transistors

2SC2688

DESCRIPTION

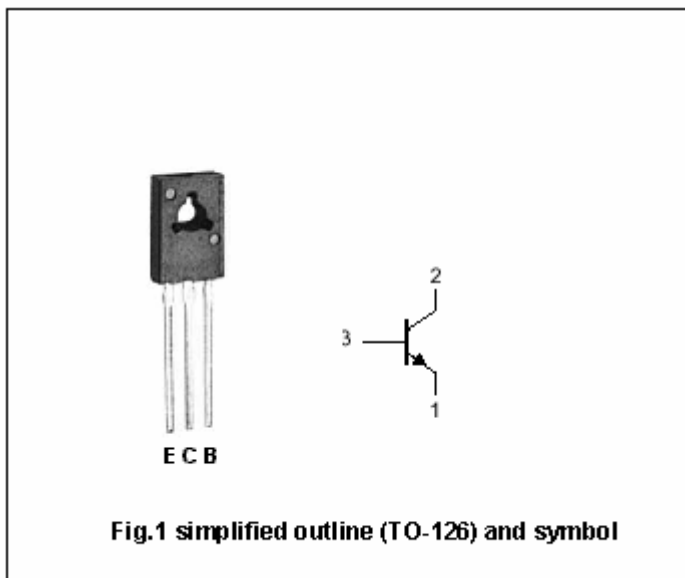
- With TO-126 package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Designed for use in Color TV chroma output circuits.

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	$T_a=25$	1.25	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA; I _B =5mA			1.5	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; I _B =0	300			V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	μA
h _{FE}	DC current gain	I _C =10mA; V _{CE} =10V	40		250	
f _T	Transition frequency	I _C =10mA; V _{CE} =30V	40			MHz
C _{re}	Feedback capacitance	I _E =0; V _{CB} =10V; f=1MHz			3.0	pF

◆ h_{FE} Classifications

N	M	L	K
40-80	60-120	100-200	160-250

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PACKAGE OUTLINE

